

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SB908

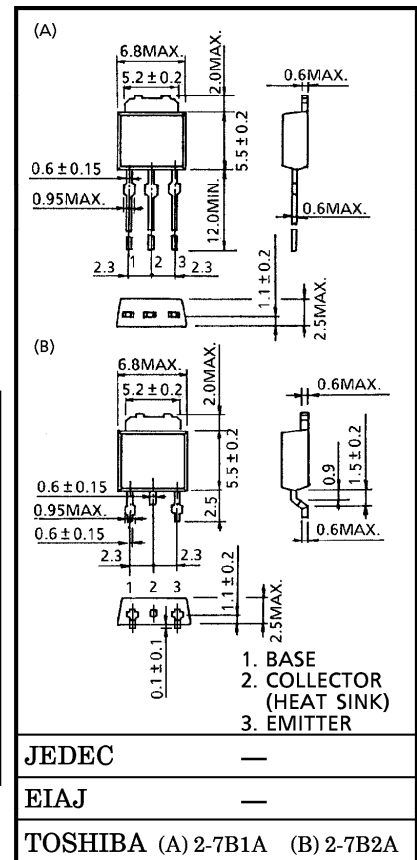
SWITCHING APPLICATIONS
 HAMMER DRIVE, PULSE MOTOR DRIVE APPLICATIONS
 POWER AMPLIFIER APPLICATIONS

- High DC Current Gain
 : $h_{FE(1)} = 2000$ (Min.) ($V_{CE} = -2V, I_C = -1A$)
- Low Saturation Voltage : $V_{CE(sat)} = -1.5V$ (Max.) ($I_C = -3A$)
- Complementary to 2SD1223.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

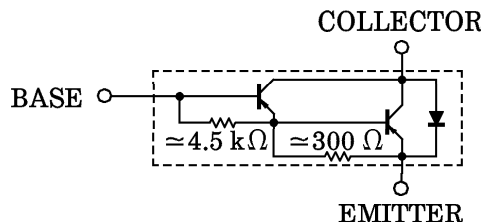
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-4	A
Base Current	I_B	-0.4	A
Collector Power Dissipation	P_C	$T_a = 25^\circ C$	1.0
		$T_c = 25^\circ C$	15
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Unit in mm



Weight : 0.36 g

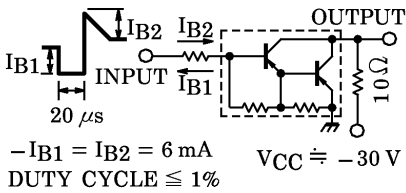
EQUIVALENT CIRCUIT



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -100\text{ V}, I_E = 0$	—	—	-20	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-2.5	mA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = -10\text{ mA}, I_B = 0$	-80	—	—	V
DC Current Gain		$h_{FE(1)}$	$V_{CE} = -2\text{ V}, I_C = -1\text{ A}$	2000	—	—	
		$h_{FE(2)}$	$V_{CE} = -2\text{ V}, I_C = -3\text{ A}$	1000	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C = -3\text{ A}, I_B = -6\text{ mA}$	—	—	-1.5	V
	Base-Emitter	$V_{BE(sat)}$	$I_C = -3\text{ A}, I_B = -6\text{ mA}$	—	—	-2.0	
Switching Time	Turn-on Time	t_{on}	 <p> $-I_{B1} = I_{B2} = 6\text{ mA}$ $V_{CC} = -30\text{ V}$ $DUTY\ CYCLE \leq 1\%$ </p>	—	0.15	—	μs
	Storage Time	t_{stg}		—	0.80	—	
	Fall Time	t_f		—	0.40	—	

